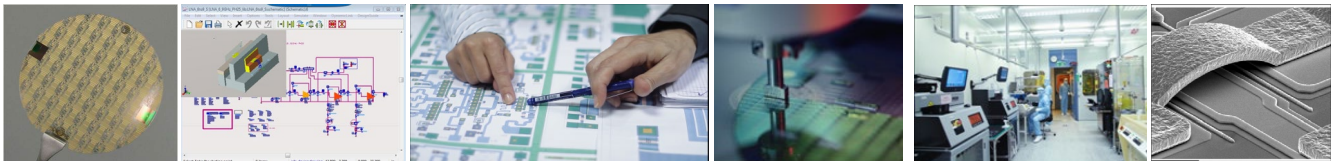


Try GaN **GH15** MPW

With UMS EUROPEAN LEADER
in RF MMIC products and foundry services



UMS launches a shared foundry run on its **GH15** GaN process.

GH15 is a 0.15µm HEMT GaN-on-SiC substrate technology for very high power applications up to 40GHz. With GH15, you will be able to design your own circuits (HPA, LNA, or more complex function). You will be supported by excellent PDK and models:

- ☑ highly accurate non-linear scalable models supporting electro-thermal capabilities,
- ☑ Stack for EM simulations,
- ☑ DRC for layout rules verification.

Offer conditions and price:

This offer is dedicated to new design concept evaluation and prototyping. The price is valid for engineering die with no screening and no test inspection.

Entry price: 3 600€/mm² for a minimum of 4mm²

The Multi-Project Wafer launch date is **November 22, 2024**.

INFORMATION	
For engineering purpose only	
Simply provide your GDS file before November 22, 2024	
DELIVERY	16 Engineering chips, from a PCM tested wafer
CONDITIONING	Gel-Pak® box
AVAILABLE DIE SIZE (mm)	1 2 3 4
MAX RATIO	1:4

Die size include 100µm dicing street - No inspection, not test on MMIC

Launching date flexibility is +/- 2 weeks

Dieframes for layout can be provided on request

Minimum order is 4mm² - Price is valid until November 22, 2024

Order to be placed before November 8, 2024

Important Notes:

- UMS may cancel the run in case of insufficient number of participants.
- For some countries a specific dedicated export license may be required before delivery.



How many dies will I receive and how much does it cost?

You will receive 16 engineering chips (untested and without visual inspection) of your circuit in Gel-Pack® box from a **GH15** PCM good wafer. The price is based on your circuit dimensions on the mask tile multiplied by the mm² unit price.

For example, if your circuit is 2 x 2 mm², the price is (2 x 2) x 3 600€ = 14 400€

GH15 MPW tile dimensions (mm)

	1	2	3	4
1	1	2	3	4
2	2	4	6	8
3	3	6	9	12
4	4	8	12	16

GH15 available die size (mm) including 100µm dicing street

Main characteristics of **GH15-11**:

Process	GH15
	High Power GaN on SiC
Active Device	HEMT
Power density	4.2W/mm
Gate Length	0.15µm
Idss sat	1.45A/mm
Vbds	>70V
Gain	13dB@30GHz
Vpinch	-3V
Gm max	405mS/mm
VdsDC	Up to 25V
Max freq use	40GHz
MIM Cap.@ 1MHz	175 pF/mm2
MIM DHD Cap. @ 1MHz	355pF/mm2
TaN Resistor	30 Ohm/sq.
TiWSi Resistor	1000 Ohm/sq.
Wafer thickness	70µm

How to participate to this shared foundry run?

More information? Ordering your GaN area? Acquisition of the GaN PDK?
Contact UMS marketing & sales department at mktsales@ums-rf.com.

